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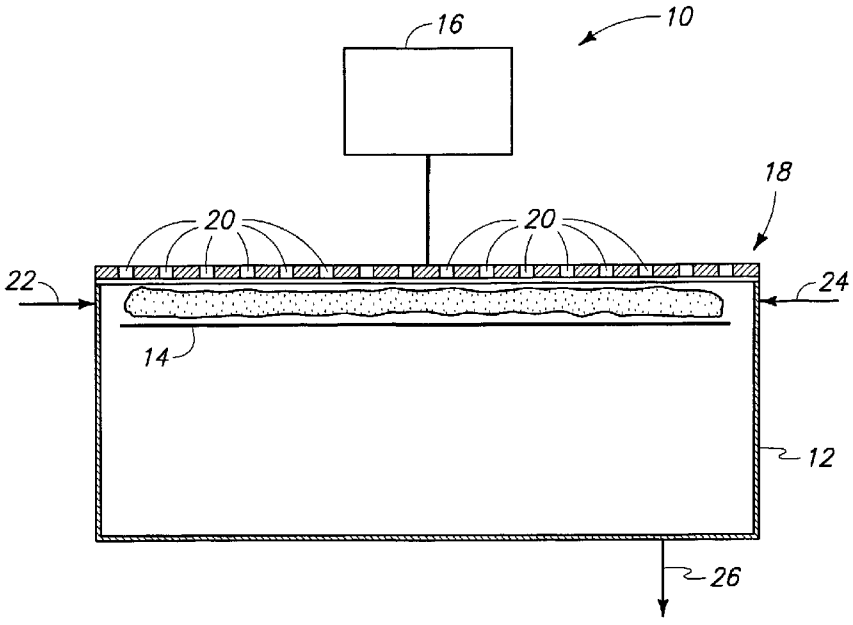
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(54) Title: ATOMIC LAYER DEPOSITION METHODS



(57) **Abstract:** A first precursor gas is flowed to the substrate within the chamber effective to form a first monolayer on the substrate. A second precursor gas different in composition from the first precursor gas is flowed to the first monolayer within the chamber under surface microwave plasma conditions within the chamber effective to react with the first monolayer and form a second monolayer on the substrate which is different in composition from the first monolayer. The second monolayer includes components of the first monolayer and the second precursor. In one implementation, the first and second precursor flowings are successively repeated effective to form a mass of material on the substrate of the second monolayer composition. Additional and other implementations are contemplated.

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